Phase analysis of quantum oscillations in graphite

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The quantum de H aas van A lphen (dH vA) and Shubnikov de H aas (SdH) oscillations m easured in graphite were decomposed by pass-band ltering onto contributions from three di erent groups of carriers. G eneralizing the theory of dH vA oscillations for 2D carriers with arbitrary spectrum and by detecting the oscillation frequencies using a method of two-dimensional phase-frequency analysis which we developed, we identied these carriers as (i) minority holes having a 2D parabolic massive spectrum $p_2^2 = 2m_2$, (ii) massive majority electrons with a 3D spectrum and (iii) majority holes with a 2D D irac-like spectrum vp₂ which seems to be responsible for the unusual strongly-correlated electronic phenomena in graphite.

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Studies of electronic properties of graphite have considerably intensi ed during the past decade because of the discovery of novel carbon-based materials such as fullerenes and nanotubes constructed from wrapped graphite sheets [1]. The quasi 2D conductivity of graphite occurs mostly inside the carbon layers due to hexagonal networks of overlapped bonds. In this single-layer approximation the Fermi surface (FS) is reduced to two points at the opposite corners of the 2D hexagonalB rillouin zone where the valence and conducting bands touch each other leading to the Dirac cone spectrum E (p) = vp, , and the charge carriers are described by the massless (2+1) dimensionalD irac fermions [2, 3, 4]. This point-like spectrum singularity and strong Coulomb coupling between ferm ions are assumed to be responsible for unusual electronic features in graphite such as, e. g., experimentally observed magnetic-elddriven m etal-insulator transition [5, 6].

However, to the best of our know ledge no unam biguous experim ental evidence for D irac ferm ions in graphite has been yet reported. In real graphite sam ples the interlayer hopping leads to pz-spectrum dispersion with opening of cigar-like FS pockets elongated along the corner edge H-K-H of the 3D hexaedronal Brillouin zone. The discussed in detail in Refs. [7, 8, 9] 3D FS has a com plicated multi-sheet structure and provides for the di erent groups of carriers. Band calculations show that in addition to the two principle majority groups of electrons (e) and holes (h) which are located close to points K and H of the Brillouin zone, several minority (m) low concentration groups carriers are possible. The nature and location of the m inority pockets are very sensitive to the param eters of the band structure calculations and to the crystalline disorder.

O ne can expect that the model of strongly interacting 2D D irac ferm ions is applicable to the real quasi 2D FS in graphite since the D irac singularity is the topologicalproperty of the electronic spectra [10] that should be stable towards the weak 3D inter-layer coupling.

In this Letter we make a comparative phase analysis of quantum de H aas van A lphen (dH vA) oscillations of the magnetization M (H) and of Shubnikov de H aas (SdH) oscillations of the resistance R (H) which provides direct evidence that the group of carriers, associated with m a jority holes (h) has the D irac singularity in the spectrum. O ther groups: (e and m) have the massive spectrum E (p) = $p_2^2 = 2m_2$.

Q uantum dH vA and SdH oscillations are the appropriate tools to study FS properties and to distinguish between di erent types of ferm ion carriers. Early m easurements of dH vA and SdH oscillations [7, 8, 9, 11] in agreement with band structure calculations demonstrated that two majority (e and h) and at least one minority (m) group of carriers exist in graphite.

To discrim inate between normal, i. e. described by the massive spectrum, and D irac fermions, we explored the rarely measured phase of quantum oscillations. Generally, phase detection encounters di culties related to interference of the contributions from dierent groups of carrier and to its sensitivity to errors in frequency determination. We overcame the problem using a speciallydeveloped two-dimensional phase-frequency analysis of its Fourier image. We distinguish also the dierent carrier groups by applying selective pass-band litering of the oscillating signal.

The magnetoresistance R (H) and magnetization M (H) data were obtained on well-characterized highly oriented pyrolytic graphite (HOPG) sample from the Union Carbide Co (HOPG-UC) as described in Ref. [5]. Brie y, low-frequency (1 H z) and dc standard four-probe magnetoresistance measurements were performed in magnetic eld 0 90 kO e applied parallel to the sample hexagonal c-axis (H k c), and at the lowest available temperature T = 2 K using Quantum Design PPM S-9T

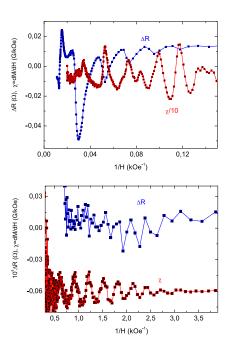


FIG.1: dHvA and SdH oscillations in graphite.Upper panel shows the region of elds 7k0 e < H < 50k0 e, characteristic for majority oscillations whereas the region of elds in low panel 0.25k0 e < H < 2.5k0 e corresponds to minority oscillations

and Janis-9T m agnet H e-cryostats. M agnetization m easurements M (H) were carried out with H k c by m eans of the SQUID m agnetom eter M PM S5 (Q uantum D esign).

Fig.1 shows the measured magnetic susceptibility = dM =dH and the oscillating part of resistance R (after substraction of the large polynom ial background R_0 (H)) as a function of the inverse magnetic eld H 1 in the high-and low-eld regions. In agreem ent with previous experiments [7, 8, 9, 11], (H^{-1}) is a superposition of at least three oscillating contributions. This can be seen in Fig. 2 where both principal peaks m_1 , e_1 and h_1 and their second harm on ic counterparts $m_2 e_2$ and h_2 in spectral intensity of Fourier transform ed susceptibility j ()j are plotted. At the same time, only the m and e peaks are seen in the spectral intensity of resistance \Re () j. In other words, the SdH h-oscillations are strongly dam ped. The corresponding oscillation frequencies i and their assignment to the dierent groups of carries which we justify below, are given in Table I. Note that unlike the widely accepted result $_{\rm h}$ < $_{\rm e}$ [11], the hole frequency h in our sample is higher then the electron frequency e•

We decomposed the measured signals (H 1) and R (H 1) onto individual m -, e- and h-oscillations, applying the frequency litering with selective pass-bands about the 1st and 2nd harm onics of the corresponding resonant frequencies $_{i}$. As shown in Fig. 3; the results demonstrate the generic behavior for quantum oscillations: an initial growth of the high-eld am plitude (low

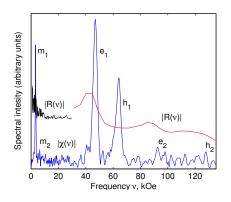


FIG.2: Spectral intensity of dH vA oscillations of susceptibility j () jand of SdH oscillations of magnetoresistance \Re () j. Peaksm _{1;2}, e_{1;2}, h_{1;2} correspond to the 1st and 2nd harm on ics of oscillations from m inority electrons, m a prity electrons and m a prity holes. The low and high frequency plots of \Re () j are obtained from di erent sets of experimental data.

TABLE I: Frequencies $_{\rm i}$ and phases $_{\rm i},$ phase factors $_{\rm i},$ $_{\rm i}$, $_{\rm i}$ and assignment of quantum oscillations in graphite.

	i (k0e)	i	i	i	i	A ssignm en	t
m inority m	3:28	0	1	1=2	0	nom alh,	2D
m ajority e	46:8	0 : 75	1	1=2	1=8	nom ale,	3D
m ajority h	64 : 1		1	0	0	D irac h,	2D

Landau levels) followed by a low - eld D ingle attenuation

 $e^{A_i=H}$. The low-intensity SdH h-oscillation are recovered from the noisy background of R () around h. The sign of R in Fig. 3 is reversed in order to recover the behavior of oscillating part of the conductivity = $\begin{pmatrix} 1 \end{pmatrix} = {2 \atop 0} R$.

To proceed with the phase detection, we analyze how the nature of the carriers in uences the phase of the quantum oscillations, by considering the quasi 2D spectrum appropriate for graphite:

$$"(p) = "_{?}(p_{?}) 2tcosp_{2}d_{B}H;$$
 (1)

where the perpendicular dispersion " $_{?}$ ($p_{?}$) can be either of the massive (parabolic) or of the Dirac (linear) type (see Table II); $_{B}$ H is the Zeeman splitting ($_{B}$ = eh=2m c).

The original theory of dH vA oscillations of Lifshitz and K osevich [12] was developed for 3D m etals with an arbitrary dispersion "(p), applied to the spectrum (1) when the energy spacing $h!_c$ between Landau levels at the FS is smaller then the characteristic dispersion t along z. The other limit of alm ost 2D electrons was studied quite recently and the general expression that incorporates both $h!_c$ t and $h!_c$ t limits was derived in [13] for the case of parabolic dispersion of "? (p?). It is straightforward to generalize the calculations of [13] for the case of arbitrary dispersion, using as in [12] the elec-

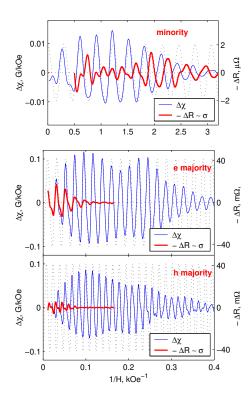


FIG.3: Quantum oscillations of susceptibility (H 1) and of resistance R (H 1) for di erent groups of carriers, obtained after two-harm onic band-pass litering of experimental data. Dot-lines show the one-harm onic phase t using the phase factors specied in Table I. The sign of R is inverted to recover the oscillating part of the conductivity .

tron orbit area S ("; p_z) = p_2^2 ("; p_z) instead of "? (p_2) and the Bohr-Som m erfeld sem iclassical quantization:

$$S(";p_z) = (n +)2 h \frac{eH}{c};$$
 (2)

where the factor 0 < 1 is related to the topology of the FS: = 1=2 for parabolic dispersion and = 0 in the D irac case [10].

Reproducing the calculations of [13] in terms of S ("; p_z) we get for the oscillating part of the magnetization:

$$M = \frac{4}{(2)^{2}} \frac{1}{hd} \frac{e}{hc} \frac{S}{dS = d''} \frac{X^{4}}{\frac{1}{l} \frac{1}{1} \sinh 1} e^{\frac{1}{h!c}^{2} \frac{1}{l}}$$
(3)
$$J_{0} \left(2 \frac{2t}{h!c}\right) \sin 2 \frac{1}{e} \frac{c}{eh} \frac{S('')}{2} + \cos 2 \frac{1}{h!c}$$

where is the impurity width of the Landau level and parameters

$$S(") = S("; =2d); = \frac{cT}{ehH}\frac{dS}{d"}$$
 1; $!_c = \frac{eH}{c}\frac{2}{dS=d"}$

are given in Table II for the norm aland D irac ferm ions.

TABLE II: Spectra, Landau quantization, areas of the quasiclassical electronic orbits and param eters of the dH vA oscillations for the m assive (N orm al) and m asseless (D irac) ferm ions

	N orm al	D irac
(p)	$p_{?}^{2} = 2m_{?}$	vjp _? j
" _? (n)	$(eh=m_{2} c) H (n + \frac{1}{2})$	(2v ² eh=c) ¹⁼² (H n) ¹⁼²
S (")	2 m _? "	$v^{2}=v^{2}$
! c	eH =am ?	ev ² H =c"
	2 ² cm _? T =ehH	2 ² cT "=hev ² H

Calculated with respect to the band origin (at $p_z =$ 0) the chem ical potential equilibrates the oscillating Ferm i-levels of di erent groups of carriers and therefore acquires the eld dependence that was shown [14] to be in portant for the very clean 2D system swith !... and in the ultra-quantum limit when only low Landau levels 1) are occupied. In the opposite case, we neglect (n this dependence and assume that = F. Note, how ever, that beats in the majority oscillations (Fig. 3) can be attributed to the conserving "cross-talk" between e and h carriers [15]. We neglect also the last oscillating spin factor in (3) since the Zeem an splitting $_{\rm B}$ H in graphite is much sm aller than the distance between Landau levels $h\! \mid_{\,\mathrm{c}}$ [11]. This tiny splitting feature is observed only in the high-eld e-oscillations in Fig.3.

Equation (3) includes both the 3D Lifshitz-K osevich lim it [12] when = $2 \frac{1^{2t}}{h!_{\circ}}$ 1, J₀() (2=)¹⁼² cos(=4) and pure 2D lim it when 1, J₀() 1. In the case of 2D D irac fermions it reduces to the result obtained in Ref. [16], whereas in the case of massive fermions the result of [13] is recovered. Analyzing only the oscillating part of M, we nd that the lst harm onic of the magnetic susceptibility

= d(M)=dH oscillates as:

$$h$$
 i
 $1 \cos 2 \frac{h}{H} l$ l+ (4)

where the factor = sign () is equal to +1 for the electrons and to 1 for the holes. The topological index (see Eq. (2)) is equal to 1=2 for massive ferm ions and is 0 for D irac ferm ions. The factor rejects the curvature of the FS in the z-direction and changes from 0 for a quasi-2D cylindrical FS when $h!_c$ t to =8 for a corrugated 3D FS when $h!_c$ t (corresponds to the contribution from minim al/maxim alcross section).

In order to determ ine factors i, i and i for each group of presented in Fig. 3 oscillations we extract the phase of their 1st harmonics 'i, analyzing Fourier-transform ed susceptibility () in the vicinity of oscillation frequencies i. Because the phase information can not be extracted from the spectral intensity plot j () j (Fig. 2), we developed the method of the 2D phase-frequency analysis that is free from the abovem en-

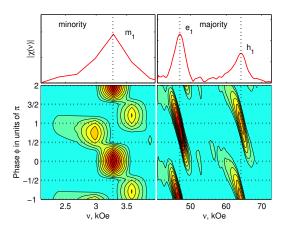


FIG. 4: Contour plot of the positive part of the phase-shift function K (;) = $\operatorname{Ree}^{i'}$ () for m inority and majority carries. Position of maxima of K (;) determ ines the oscillation frequencies $_{i}$ and phases $_{i}$ for di erent groups of carriers. Upper panel presents the corresponding spectral intensity j ()j.

tioned phase/frequency uncertainty. For its illustration we assume that close to the resonance frequency $_0$ the Fourier-transformed susceptibility has the Gaussian-like prole () $e^{i' \circ} e^{-(0)^2}$. Constructing now the phase-shift function K (';) = Ree i' () that in our model case is equal to $e^{-(0)^2} \cos(-0)$ we can detect both the frequency $_0$ and the phase '_0 simultaneously as the position of the maximum of K (';) in the plane -.

The phase-shift function for the dHvA oscillations in graphite is shown in Fig. 4. Determination of maxima of K (';) gives the collected in Table I oscillation frequencies $_{\rm i}$ and their phases ' $_{\rm i}$ more precisely than the previous determination: ($_{\rm e} = _{\rm h} = 0.75$ in [8] and $_{\rm h} = 0.76$, $_{\rm e} = 0.64$ in [9]).

By analyzing the oscillations of and (Fig. 3), and taking into account the relation $jn jH^2$ [17], we conclude that the in- and out-of-phase behavior corresponds to electrons and holes with = +1 and = 1, respectively. For h-carriers this analysis was independently supported by a comparison between the longitudinal resistance oscillations R and of the Hall resistance R _H (not shown): for holes, m inim a in R should correspond to m inim a in R _H [11], and this is what we observed.

K now ledge of i and i allows the unam biguous determ ination of the factors i (i = 1=2 or 0) and i ($j_i j < 1=8$) that are intermelated as:

$$i = (sign_{i} 2_{i}l + 2_{i})$$
 (5)

The analysis of the 1th harm onic parameters $_{i}$, $_{i}$ and $_{i}$, given in Table I for each group of carriers, led us to

the following conclusions.

(i) The m inority carriers are holes with a 2D m assive parabolic spectrum .

(ii) The majority electrons have the parabolic spectrum with 3D $\ensuremath{p_z}$ -dispersion.

(iii) The majority holes are 2D D irac ferm ions.

The identi cation of D irac ferm ions which can be responsible for unusual strongly-correlated electronic phenom ena in graphite [5, 6] is the principal result of this work.

The method proposed here for the two-dimensional phase-frequency analysis allows the e cient phase definition in any quantum oscillation phenomena, including those in low-dimensional organic conductors, in the mixed state of superconductors and in 2D quantum Hall sem iconductors.

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